

Radio-Frequency IC Design

Lecture 7: LNA Design

ELEC 404



©Sudip Shekhar

Not to be copied, used, or revised without explicit written permission from the copyright owner.

Example Specifications

- **Operating frequency f_0 and BW:**
- **Minimum voltage gain (A_v or S_{21}): $\sim 15\text{dB}$**
- **Input Matching to $50/100\Omega$: $S_{11} < -10\text{dB}$**
- **Maximum Power Consumption: $\sim 5\text{-}10\text{mW}$**
- **Maximum NF: $\sim 2\text{-}4\text{dB}$**
- **Minimum IIP3: $\sim 0\text{dBm}$**
- **1dB compression point: $\sim -10\text{dBm}$**
- **Supply Voltage V_{dd}**

Pick Q_{in} at the Input Network

- Find Q_{in} for minimum S_N
- If gate-induced noise is ignored (!), “maximize” Q_{in} while meeting gain, linearity and BW specs
- Obtain Q_{in} from BW specification.

Find W of the Main CS Transistor

- **With Q_{in} , C_{ox} and L_{min} , calculate W .**

Find g_m of the Main CS Transistor

- Plot g_m , g_{ds} , V_{gs} vs. current density of the NMOS
- Operate the NMOS in weak to moderate inversion for noise vs. linearity tradeoff.
- With I_{den} and $V_{gs} - V_{th}$, calculate normalized- g_m .

- With normalized- g_m and W , calculate g_m .

Is the Gain Adequate?

- Compare the two values of g_m of Main CS transistor

Find L_s

- Find f_T and L_s :

Find L_g

- Calculate L_g from f_0 :

